

On performance limitations and property correlations of Al-doped ZnO deposited by radio-frequency sputtering - DTU Orbit (09/11/2017)

On performance limitations and property correlations of Al-doped ZnO deposited by radio-frequency sputtering: Paper The electrical properties of RF-sputtered Al-doped ZnO are often spatially inhomogeneous and strongly dependent on deposition parameters. In this work, we study the mechanisms that limit the minimum resistivity achievable under different deposition regimes. In a low- and intermediate-pressure regime, we find a generalized dependence of the electrical properties, grain size, texture, and Al content on compressive stress, regardless of sputtering pressure or position on the substrate. In a high-pressure regime, a porous microstructure limits the achievable resistivity and causes it to increase over time as well. The primary cause of inhomogeneity in the electrical properties is identified as energetic particle bombardment. Inhomogeneity in oxygen content is also observed, but its effect on the electrical properties is small and limited to the carrier mobility.

General information

State: Published

Organisations: Department of Micro- and Nanotechnology, Silicon Microtechnology, Department of Energy Conversion and Storage, Fundamental Electrochemistry, Department of Photonics Engineering, Optical Microsensors and Micromaterials, Department of Physics, Experimental Surface and Nanomaterials Physics, Technical University of Denmark

Authors: Crovetto, A. (Intern), Ottsen, T. S. (Ekstern), Stamate, E. (Intern), Kjær, D. (Intern), Schou, J. (Intern), Hansen, O.

(Intern)

Number of pages: 11 Publication date: 2016

Main Research Area: Technical/natural sciences

Publication information

Journal: Journal of Physics D: Applied Physics

Volume: 49 Issue number: 29 Article number: 295101 ISSN (Print): 0022-3727

Ratings:

BFI (2017): BFI-level 1

Web of Science (2017): Indexed yes

BFI (2016): BFI-level 1

Scopus rating (2016): CiteScore 2.07 SJR 0.645 SNIP 0.917

Web of Science (2016): Indexed yes

BFI (2015): BFI-level 1

Scopus rating (2015): SJR 0.693 SNIP 1.046 CiteScore 2.1

Web of Science (2015): Indexed yes

BFI (2014): BFI-level 1

Scopus rating (2014): SJR 1.069 SNIP 1.383 CiteScore 2.53

Web of Science (2014): Indexed yes

BFI (2013): BFI-level 1

Scopus rating (2013): SJR 1.18 SNIP 1.469 CiteScore 2.6

ISI indexed (2013): ISI indexed yes Web of Science (2013): Indexed yes

BFI (2012): BFI-level 1

Scopus rating (2012): SJR 1.244 SNIP 1.394 CiteScore 2.31

ISI indexed (2012): ISI indexed yes Web of Science (2012): Indexed yes

BFI (2011): BFI-level 1

Scopus rating (2011): SJR 1.257 SNIP 1.399 CiteScore 2.36

ISI indexed (2011): ISI indexed yes Web of Science (2011): Indexed yes

BFI (2010): BFI-level 1

Scopus rating (2010): SJR 1.291 SNIP 1.288

Web of Science (2010): Indexed yes

BFI (2009): BFI-level 1

Scopus rating (2009): SJR 1.283 SNIP 1.337

Web of Science (2009): Indexed yes

BFI (2008): BFI-level 2

Scopus rating (2008): SJR 1.446 SNIP 1.563

Web of Science (2008): Indexed yes

Scopus rating (2007): SJR 1.385 SNIP 1.633

Web of Science (2007): Indexed yes

Scopus rating (2006): SJR 1.398 SNIP 1.699

Web of Science (2006): Indexed yes

Scopus rating (2005): SJR 1.203 SNIP 1.466

Web of Science (2005): Indexed yes

Scopus rating (2004): SJR 1.123 SNIP 1.442

Web of Science (2004): Indexed yes Scopus rating (2003): SJR 0.9 SNIP 1.2 Web of Science (2003): Indexed yes Scopus rating (2002): SJR 0.99 SNIP 1.221

Web of Science (2002): Indexed yes

Scopus rating (2001): SJR 0.901 SNIP 1.205

Web of Science (2001): Indexed yes Scopus rating (2000): SJR 0.79 SNIP 1.133 Web of Science (2000): Indexed yes

Scopus rating (1999): SJR 0.925 SNIP 1.249

Original language: English

ZnO,, AZO, Sputtering, Stress, Correlations, Line profile analysis, Bombardment

Electronic versions:

AZO_distributions_postprint.pdf. Embargo ended: 24/06/2017

DOIs:

10.1088/0022-3727/49/29/295101

Source: FindIt Source-ID: 277732739

Publication: Research - peer-review > Journal article - Annual report year: 2016